Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A ferroelectric thin film formed of crystals in which directions of polarization axes are inconsistent with an applied electric field direction in a crystal system.

2. (Original) A ferroelectric thin film formed of crystals in which directions of 180° domains are inconsistent with an applied electric field direction in a crystal system.

3. (Original) A ferroelectric thin film formed of crystals in which directions of 90° domains are inconsistent with a direction perpendicular to an applied electric field direction in a crystal system.

4. (Previously Amended) The ferroelectric thin film as defined in claim 1, wherein the 180° domains are arranged at a constant angle to the applied electric field direction.

5. (Currently Amended) The ferroelectric thin film as defined in <u>claim 1</u>, wherein the 90° domains are arranged at a constant angle to the applied electric field direction.

6. (Previously Amended) The ferroelectric thin film as defined in claim 1, wherein the 180° domains reversely rotate in a predetermined electric field with respect to the applied electric field direction and a ferroelectric thin film plane.

7. (Previously Amended) The ferroelectric thin film as defined in claim 1, wherein the 90° domains reversely rotate in a predetermined electric field with respect to the applied electric field direction and a ferroelectric thin film plane.

8. (Previously Amended) The ferroelectric thin film as defined in claim 1, wherein polarization is arranged at a constant angle to the applied electric field direction have the same polarization in the same applied electric field.

9. (Previously Amended) The ferroelectric thin film as defined in claim 1, formed of a polycrystal highly oriented in the applied electric field direction in a ferroelectric thin film plane.

10. (Previously Amended) The ferroelectric thin film as defined in claim 1, wherein a polarization axis distribution exhibits no anisotropy with respect to the applied electric field direction in a ferroelectric thin film plane.

11. (Previously Amended) The ferroelectric thin film as defined in claim 1, using: a tetragonal $Pb(Zr,Ti)O_3$ ferroelectric which is (111)-oriented along the applied electric field direction with respect to a ferroelectric thin film plane.

12. (Previously Amended) The ferroelectric thin film as defined in claim 1, using: a rhombohedral $Pb(Zr,Ti)O_3$ ferroelectric which is (001)-oriented along the applied electric field direction with respect to a ferroelectric thin film plane.

13. (Previously Amended) The ferroelectric thin film as defined in claim 1, using: a bismuth-layer-structured ferroelectric which is (111) or (110)-oriented along the applied electric field direction with respect to a ferroelectric thin film plane.

14. (Previously Amended) The ferroelectric thin film as defined in claim 1, using: an $SrBi_2Ta_2O_9$ ferroelectric which is (115), (111), or (110)-oriented along the applied electric field direction with respect to a ferroelectric thin film plane.

15. (Previously Amended) The ferroelectric thin film as defined in claim 1, using: a $Bi_4T_3O_{12}$ ferroelectric which is (117), (111), (107), or (317)-oriented along the applied electric field direction with respect to a ferroelectric thin film plane.

16. (Original) The ferroelectric thin film as defined in claim 11, using a (111)-oriented platinum group metal electrode with a full width half maximum of 2° or less.

17. (Original) The ferroelectric thin film as defined in claim 12, using a (001)-oriented platinum group metal electrode with a full width half maximum of 2° or less.

18. (Original) The ferroelectric thin film as defined in claim 13, using a (111)-oriented platinum group metal electrode with a full width half maximum of 2° or less.

19. (Original) The ferroelectric thin film as defined in claim 14, using a (111)-oriented platinum group metal electrode with a full width half maximum of 2° or less.

20. (Original) The ferroelectric thin film as defined in claim 15, using a (111)-oriented platinum group metal electrode with a full width half maximum of 2° or less.

21. (Original) The ferroelectric thin film as defined in claim 13, using a (110)-oriented platinum group metal electrode with a full width half maximum of 2° or less.

22. (Original) The ferroelectric thin film as defined in claim 14, using a (110)-oriented platinum group metal electrode with a full width half maximum of 2° or less.

23. (Original) The ferroelectric thin film as defined in claim 15, using a (110)-oriented platinum group metal electrode with a full width half maximum of 2° or less.

24. (Previously Amended) The ferroelectric thin film as defined in claim 16, using an alloy electrode of lead and platinum group metal.

25. (Previously Amended) The ferroelectric thin film as defined in claim 1, formed by using a mixed solution of a sol-gel solution and an metal organic decomposition solution.

26. (Previously Amended) The ferroelectric thin film as defined in claim 1, comprising silicon, or silicon and germanium in elements of ferroelectric.

27. (Previously Amended) A method of manufacturing the ferroelectric thin film as defined in claim 1, comprising:

performing crystallization by rapid heating in an oxidizing gas atmosphere at a pressure less than 10 atmospheres.

28. (Previously Amended) A ferroelectric memory device using the ferroelectric thin film as defined in claim 1.

29. (Previously Amended) A ferroelectric piezoelectric device using the ferroelectric thin film as defined in claim 1.